

Numerical investigations of the multi-layer graphene as a thermal interface material and an elector-magnetic field shield layer for 3D power supply on chip applications

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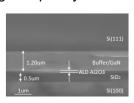
Si(100)



INTRODUCTION

Advantages of 3D Power SoC

- · High efficiency at high frequency switching
- High power density (miniaturization)



Direct bonding of GaN - Si(100) [1]

Power device Insulator Passive Insulator Control circuit Si substrate Heat spreader and

Passivation

Heat sink

3D power SoC [2]

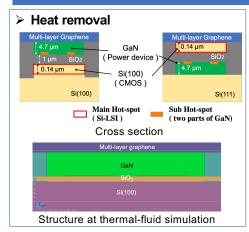
> Challenges

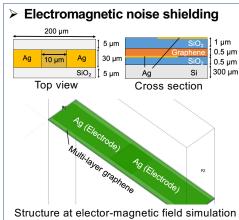
- · Heterogenous integration
- · Heat removal
- · Electromagnetic noise shielding

Multi-layer graphene

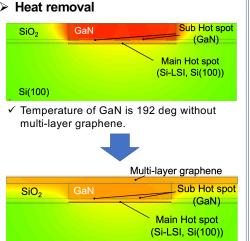
[1] R. Ishito, K. Ono, and S. Matsumoto, IEEE CPMT Symposium Japan 2019, ECR Session 12, 2019. [2] K. Hiura, Y. Ikeda, Y. Hino, and S. Matsumoto, Japanese J Applied Physics, vo.56, 04CR13, 2017.

DESIGN DETAILS

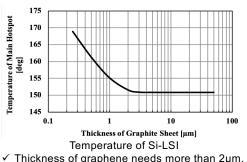




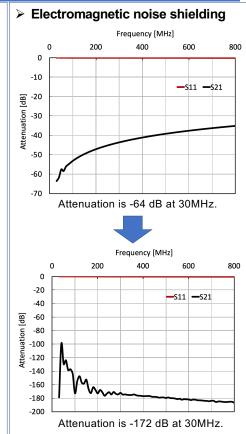
SIMULATION RESULTS



✓ Temperature of GaN is 174 deg with multi-layer graphene.



Si-LSI
✓ Noise attenuation with multi-layer graphene is 108 dB higher than without it.



CONCLUSIONS

- ✓ We can remove the heat of hot-spot in GaN power device by putting GaN on Si-LSI and using multi-layer graphene.
- ✓ Multi-layer graphene enables to shield electromagnetic noise.

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